



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

EMH2407 — N-Channel Silicon MOSFETs General-Purpose Switching Device Applications

Features

- Low ON-resistance
- Best suited for LiB charging and discharging switch
- Common-drain type
- 2.5V drive
- Protection diode in

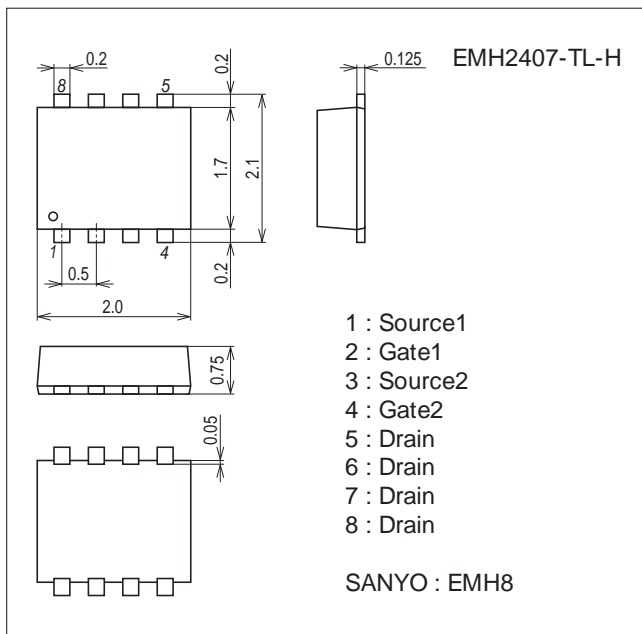
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	I _D		6	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	40	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.3	W
Total Dissipation	P _T	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.4	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Package Dimensions

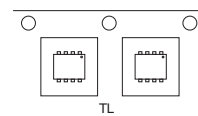
unit : mm (typ)
7045-006



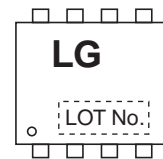
Product & Package Information

- Package : EMH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

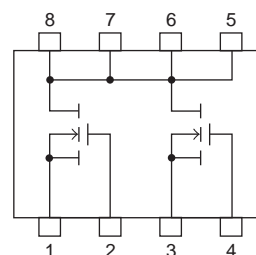
Packing Type : TL



Marking



Electrical Connection

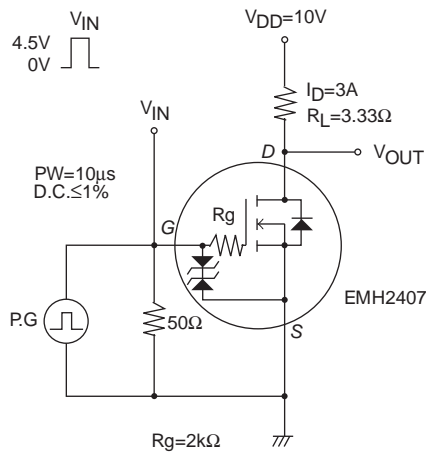


EMH2407

Electrical Characteristics at Ta=25°C

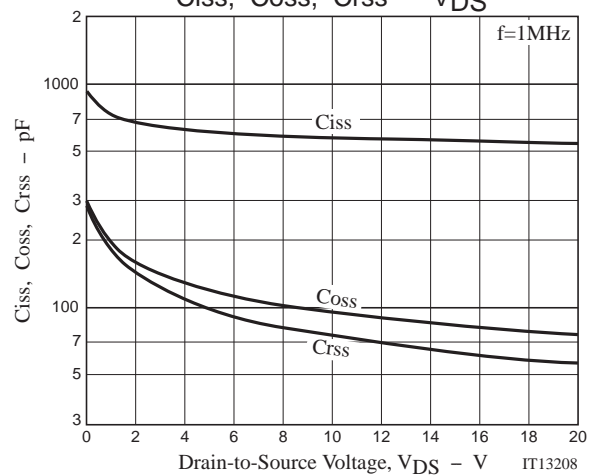
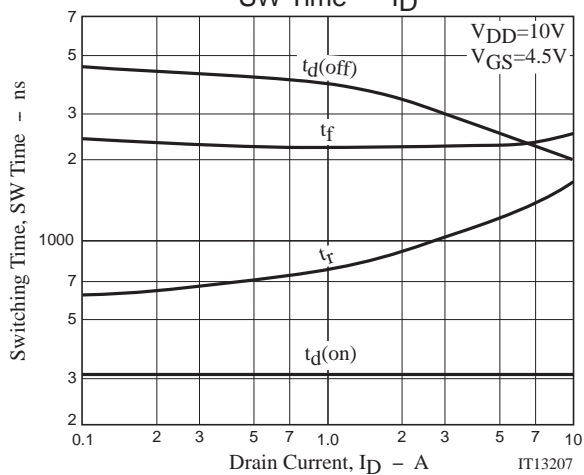
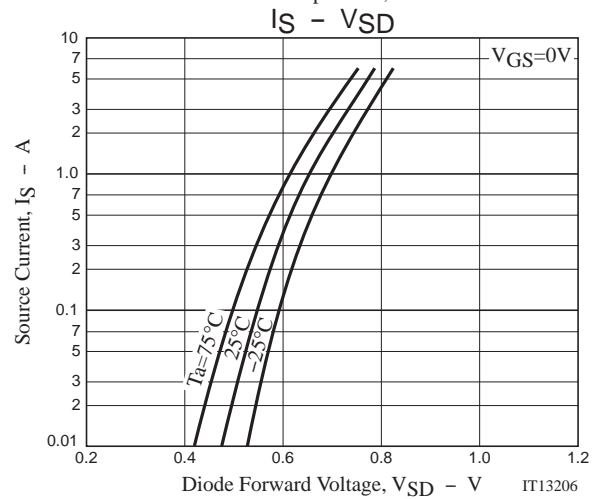
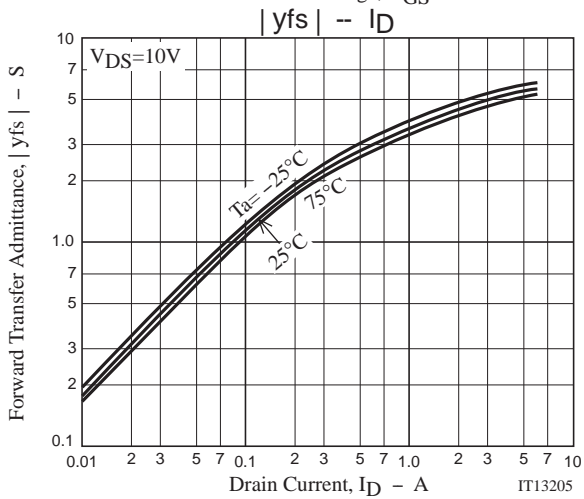
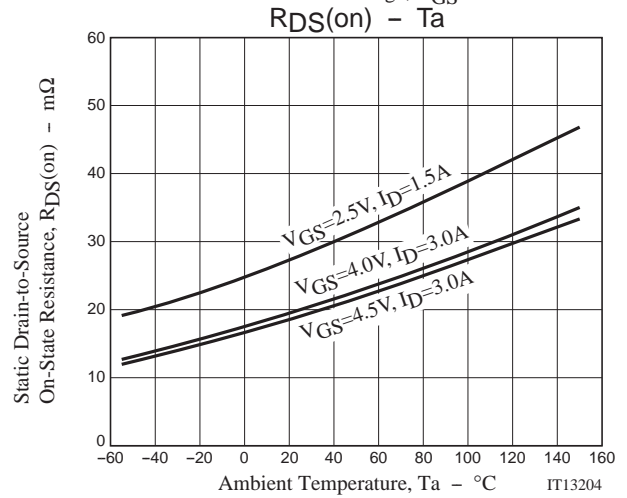
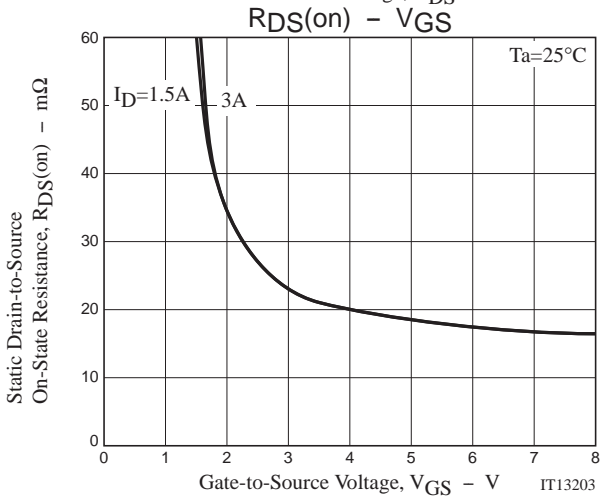
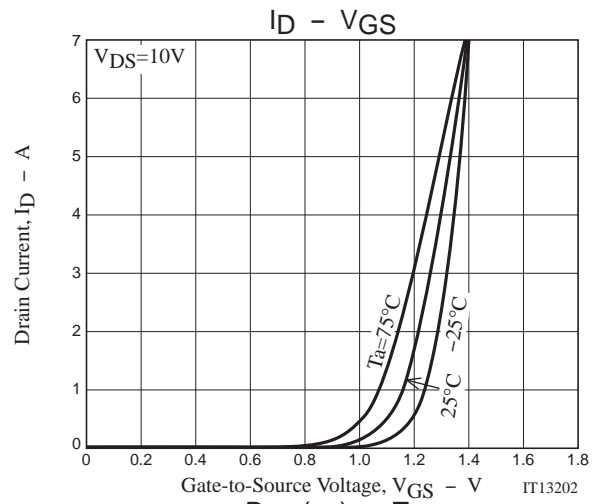
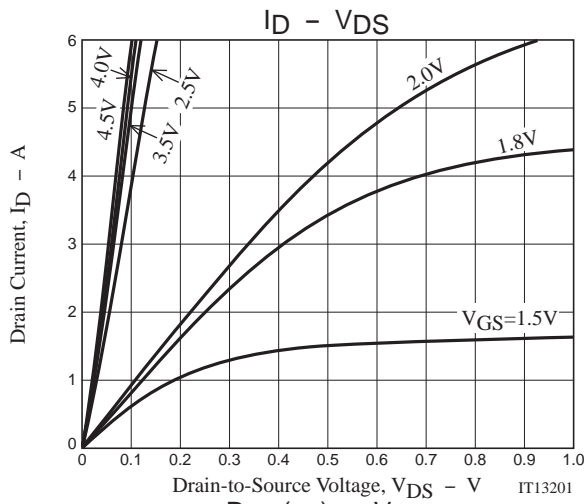
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	0.5		1.3	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =3A	3	5		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =3A, V _{GS} =4.5V	13	19	25	mΩ
	R _{DS(on)2}	I _D =3A, V _{GS} =4V	14	20	26	mΩ
	R _{DS(on)3}	I _D =1.5A, V _{GS} =2.5V	16	28	39	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		580		pF
Output Capacitance	C _{oss}			95		pF
Reverse Transfer Capacitance	C _{rss}			75		pF
Turn-ON Delay Time	t _{d(on)}		See specified Test Circuit.		310	
Rise Time	t _r			1020		ns
Turn-OFF Delay Time	t _{d(off)}			3000		ns
Fall Time	t _f			2250		ns
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V, I _D =6A			6.3	
Gate-to-Source Charge	Q _{gs}			0.83		nC
Gate-to-Drain "Miller" Charge	Q _{gd}			1.9		nC
Diode Forward Voltage	V _{SD}	I _S =6A, V _{GS} =0V		0.78	1.2	V

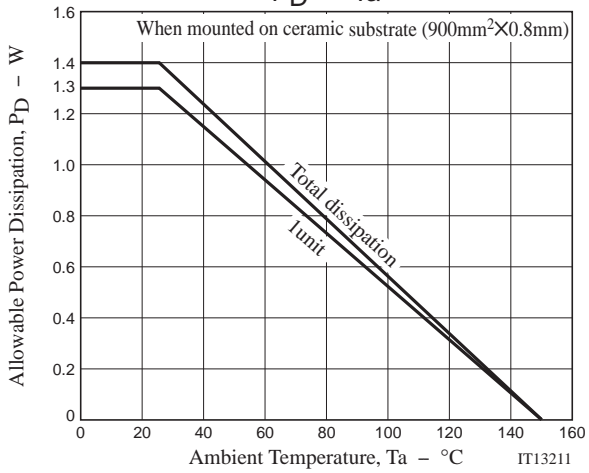
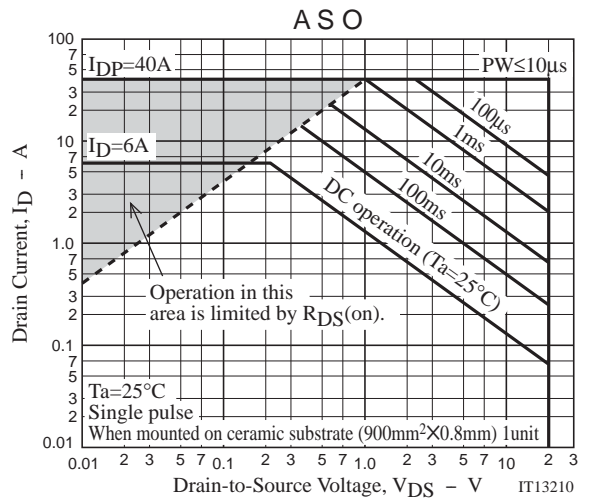
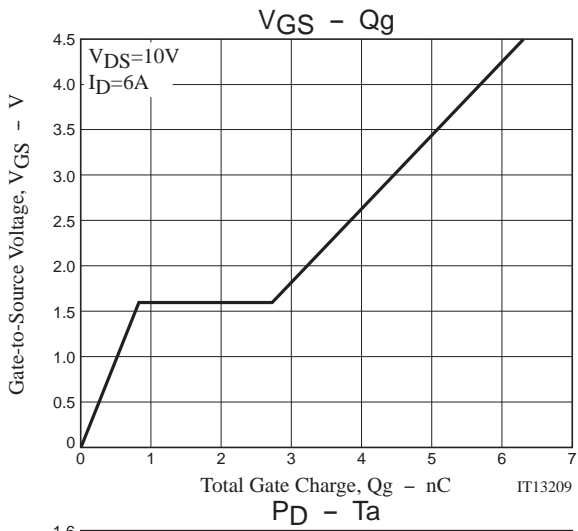
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
EMH2407-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free





EMH2407

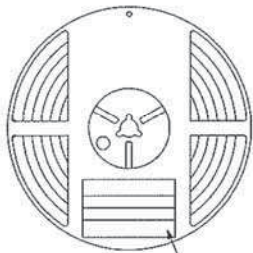
Embossed Taping Specification

EMH2407-TL-H

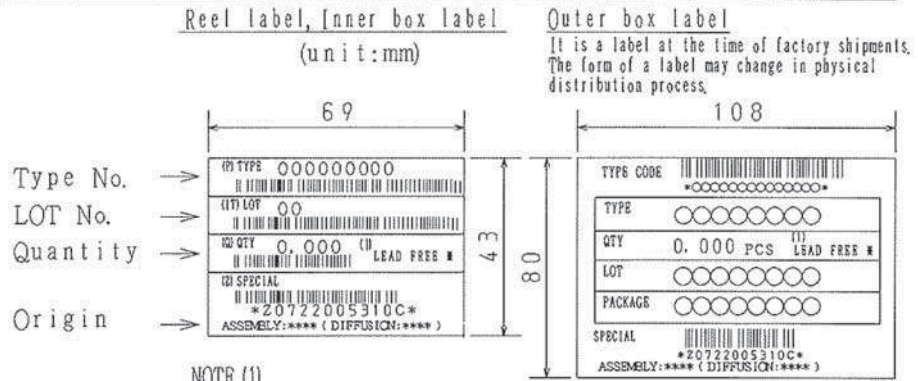
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
EMH8	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label



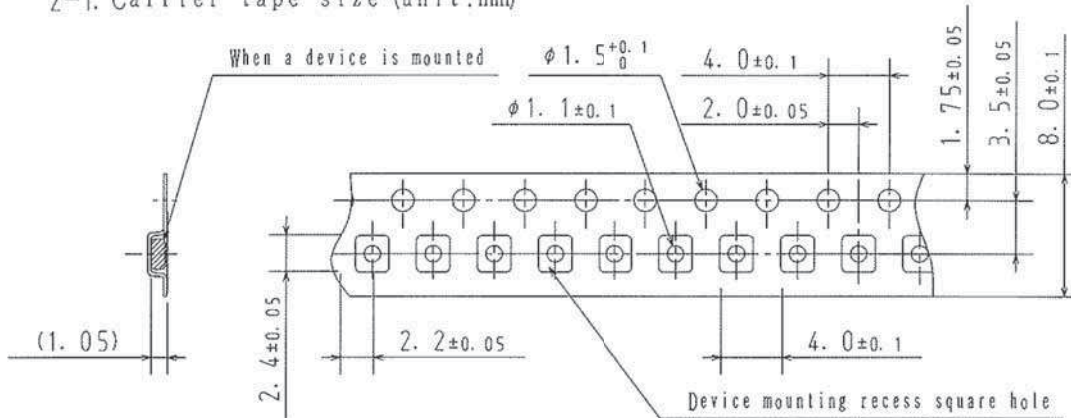
NOTE (1)

The LEAD FREE description shows that the surface treatment of the terminal is lead free.

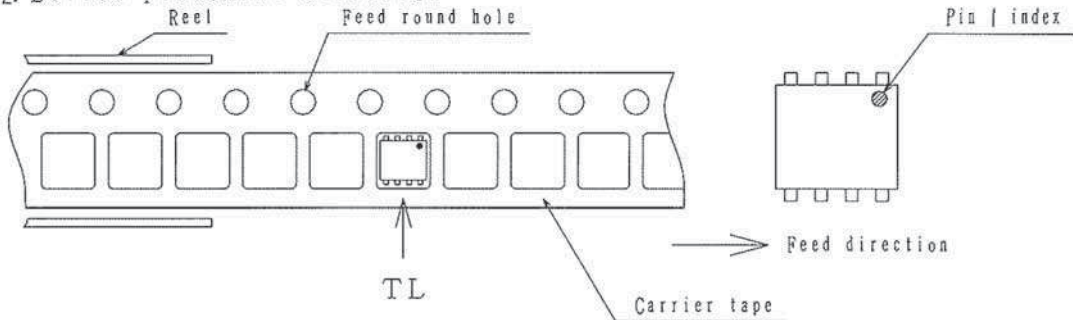
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

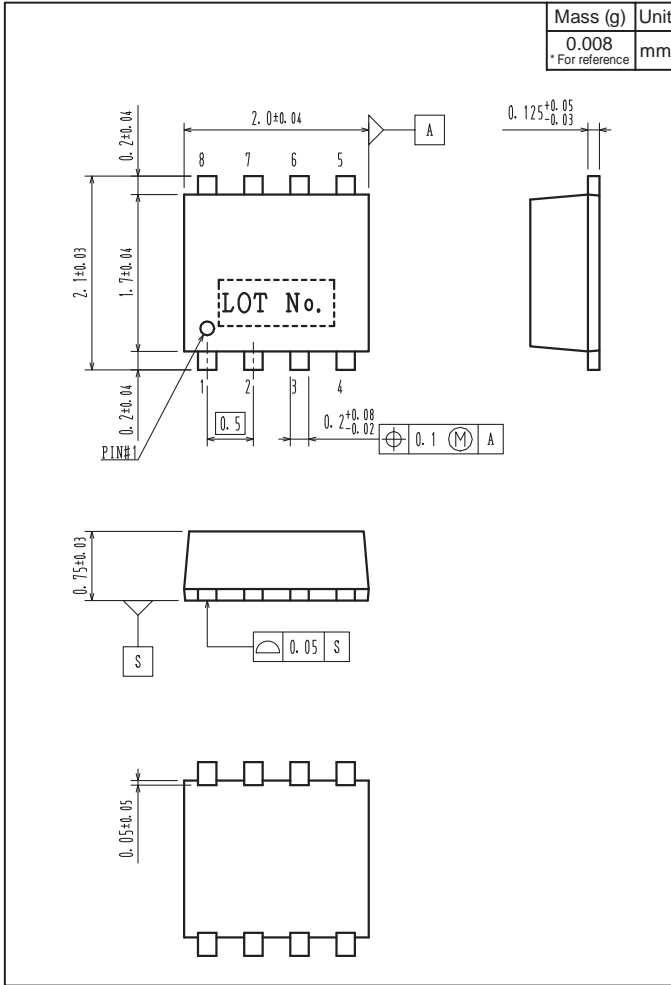


Those with pin 1 index on the feed hole side.....TL

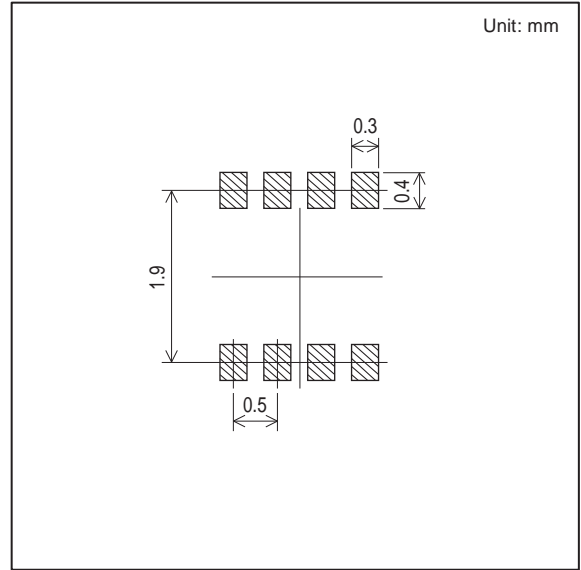
EMH2407

Outline Drawing

EMH2407-TL-H



Land Pattern Example



Note on usage : Since the EMH2407 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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